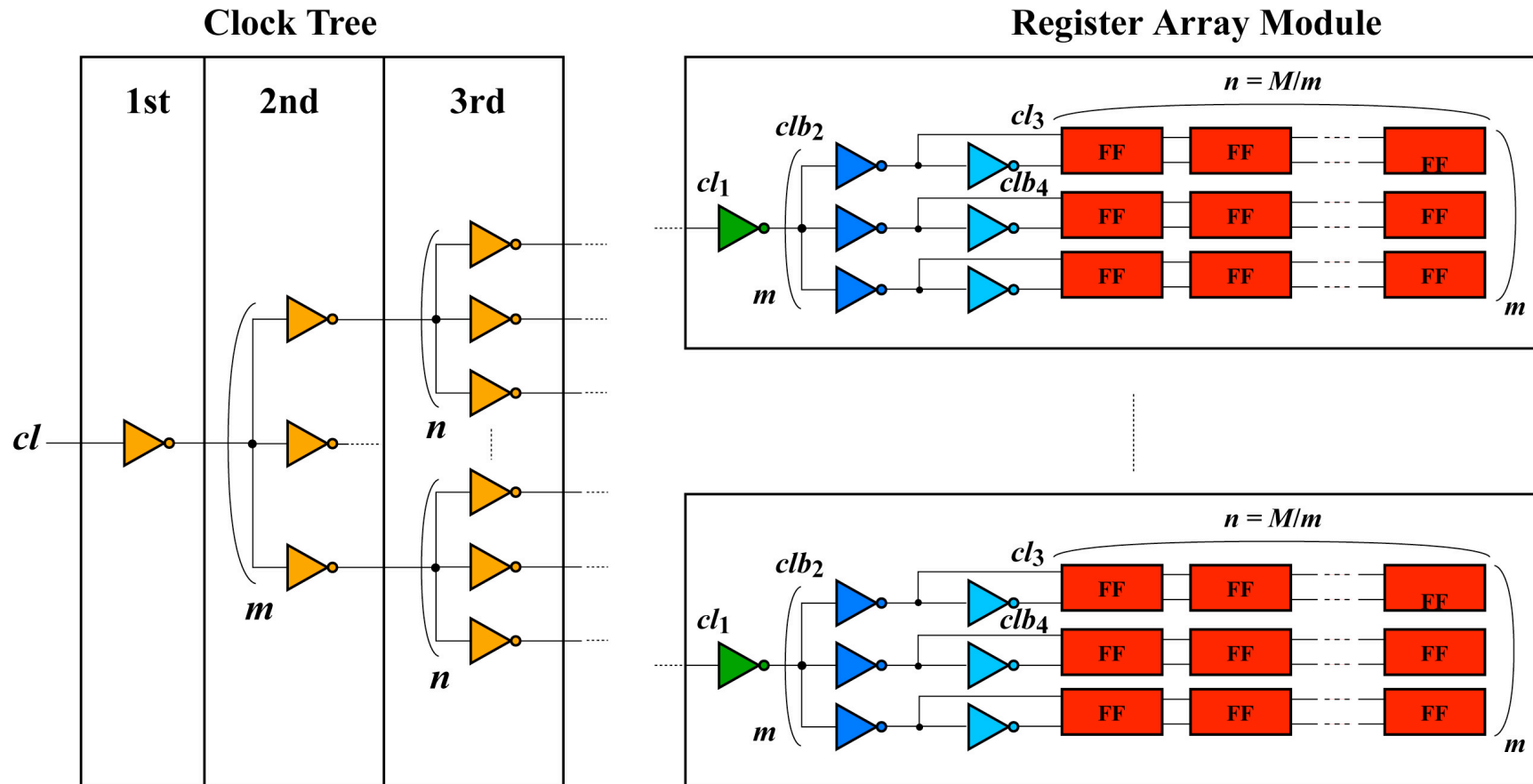


Low-Power High-Speed 90-nm CMOS Clock Drivers

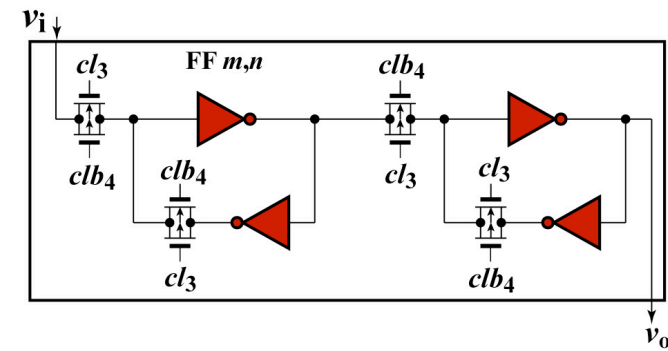
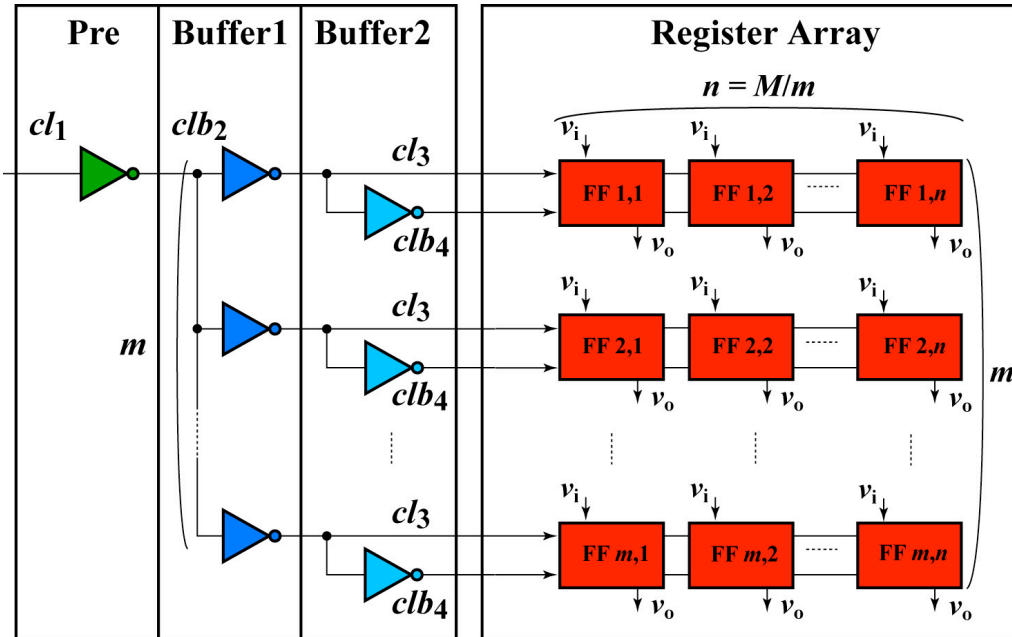
T. Enomoto, S. Nagayama and N. Kobayashi

Chuo University, Tokyo, Japan

ASP-DAC'2007, Yokohama, Japan, Jan. 24, 2007



Register Array Modules



Technology: 90-nm, Triple-Well, 6-Layer, Cu, CMOS

Gate Lengths: $L_n = L_p = 0.1 \mu\text{m}$

Channel Widths (Logic): $W_n = 1.08 \mu\text{m}, W_p = 1.64 \mu\text{m}$

Channel Widths (Swich): $W_n = 0.54 \mu\text{m}, W_p = 0.82 \mu\text{m}$

Threshold Voltages: $V_{tn} = 0.222 \text{ V}, V_{tp} = -0.241 \text{ V}$

No. of D-FF ($M = m \times n$) = 40

m	$n = M/m$
1	40
5	8
8	5
10	4
20	2
40	1

Power Dissipation and Signal Propagation Delay of a Single Logic Gate

Power due to dynamic current

$$p_D(n) = (An+B) \cdot V_D^2 \cdot f$$

Power due to short-circuit current

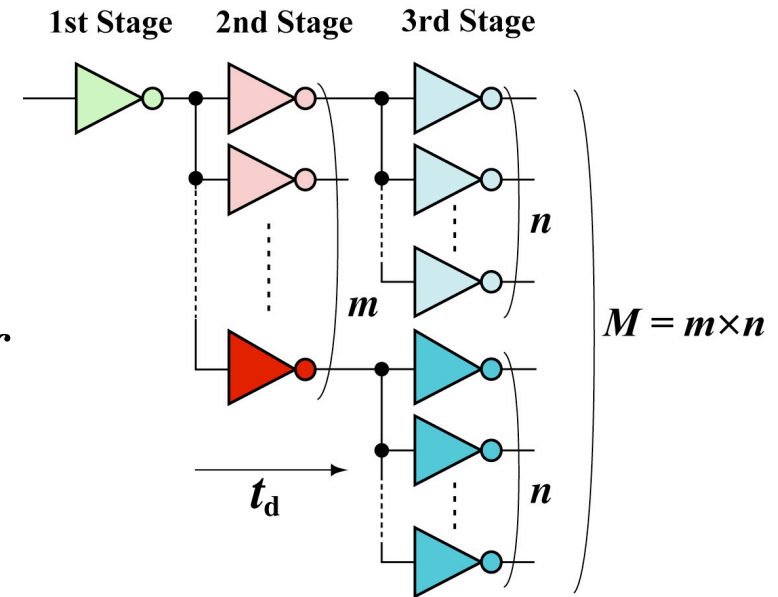
$$p_S(m, n) = \frac{E(m+F)^G \cdot (V_D - 2V_T)^3 \cdot f}{(1+Hn)^J}$$

Signal Propagation Delay

$$t_d \approx \frac{(C_m + C_n)V_D^2}{\frac{\beta}{2}(V_D - V_{th})^2} \approx \frac{2(C_m + C_n)}{\beta(V_D - V_{th})}$$

$$\propto (Am + B) + (An + B) = A(m + n) + 2B$$

$$= A\left(m + \frac{M}{m}\right) + 2B$$



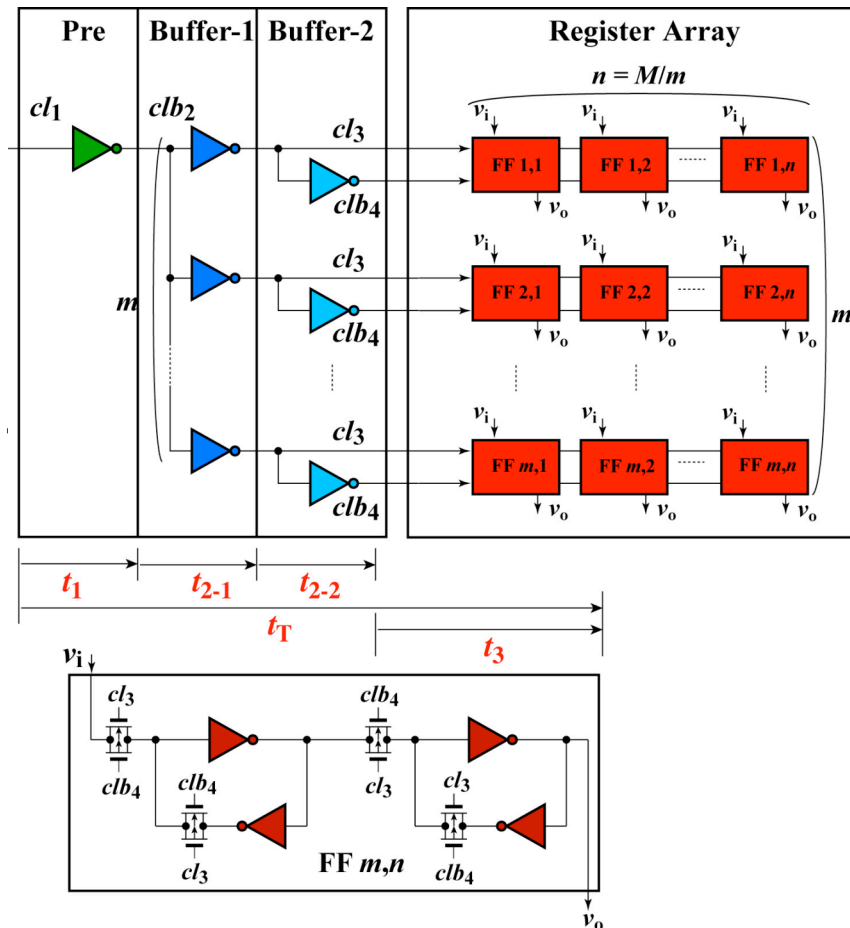
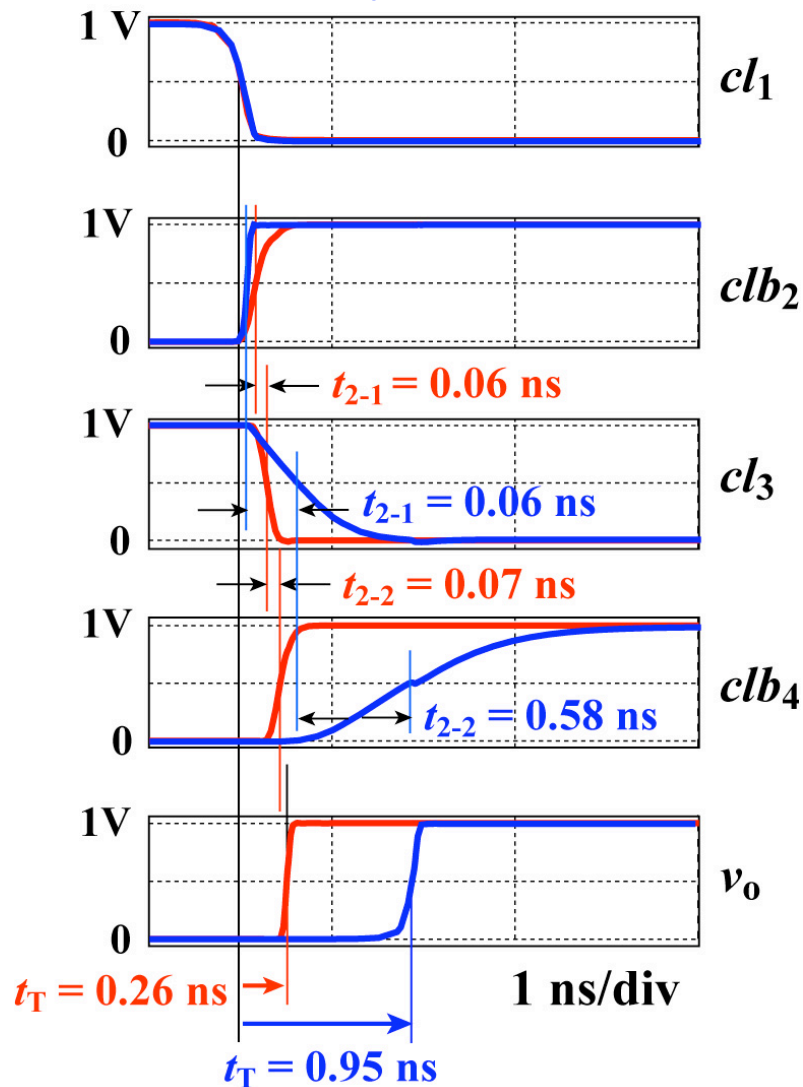
at $m = 1$ & $m = M$
 $t_d \propto A(M+1) + 2B$

at $m = n$
 $t_d \propto 2AM^{0.5} + 2B$

Signal Propagation Delay of 90-nm Register Array Modules (SPICE Simulation)

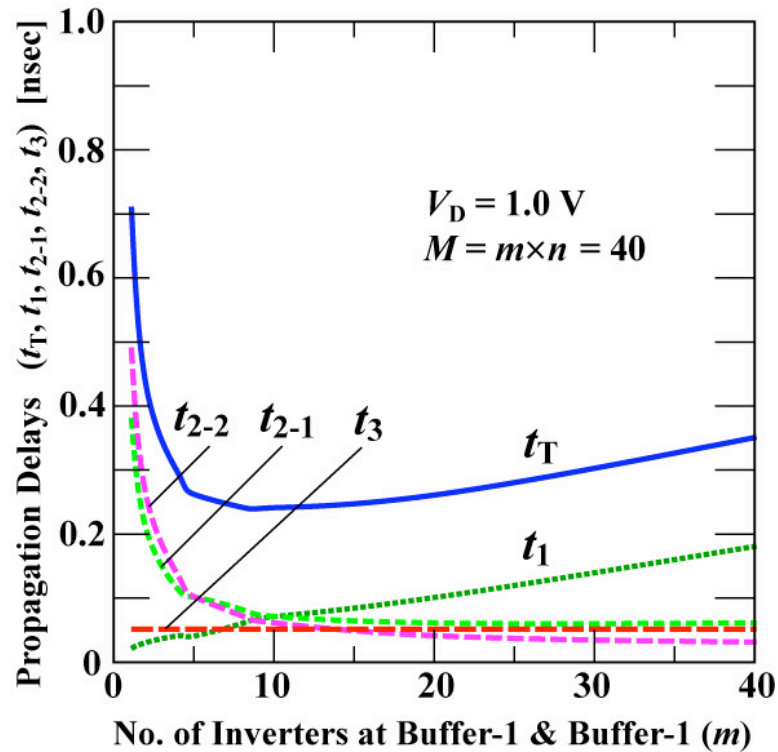
$m=1$ $m=10$
 $n=40$ $m=4$

No. of D-FF ($M = m \times n$) = 40

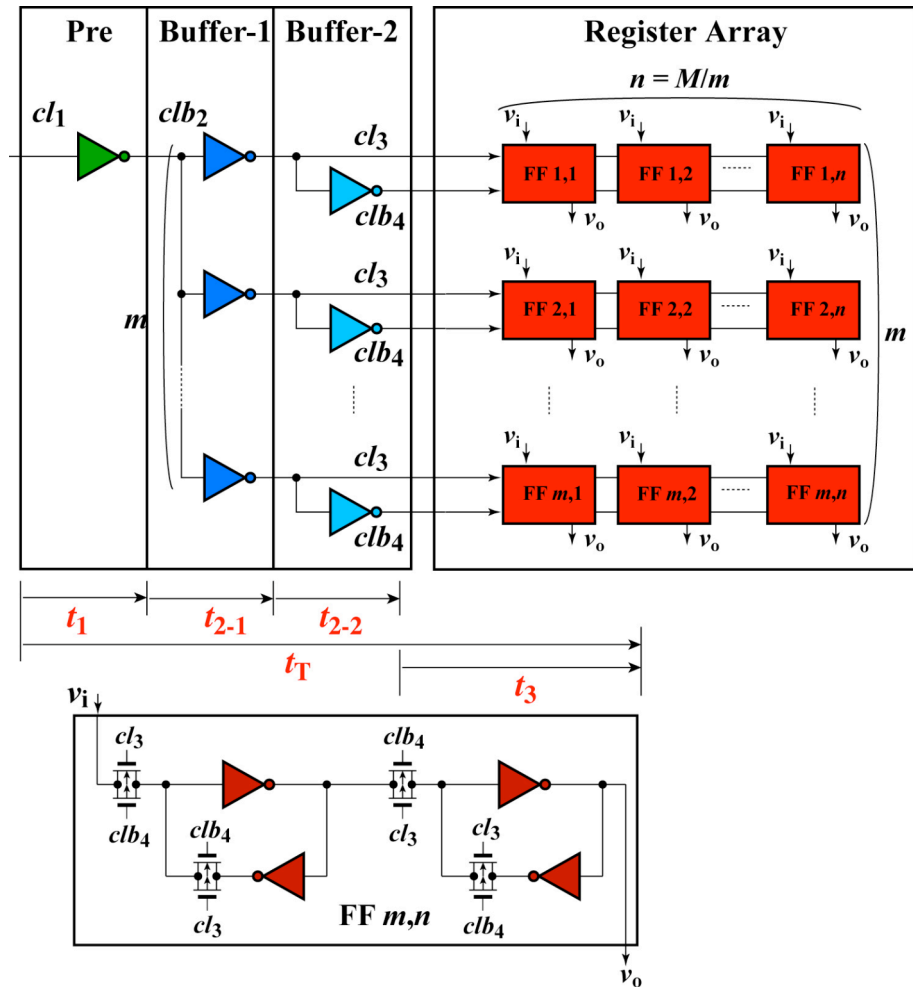


t_T is considerably reduced

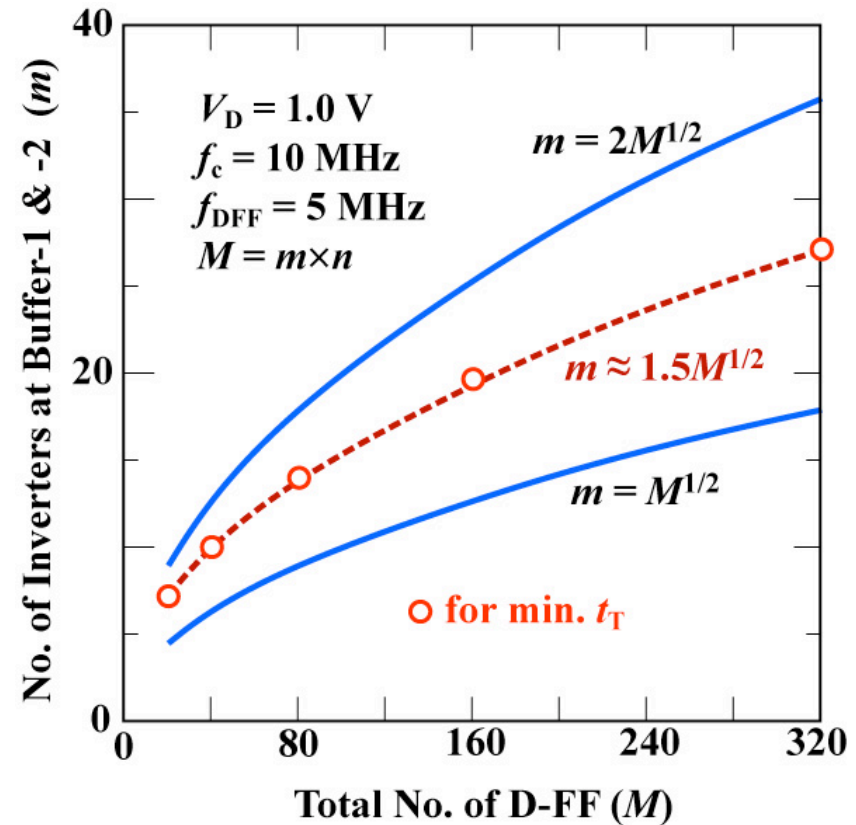
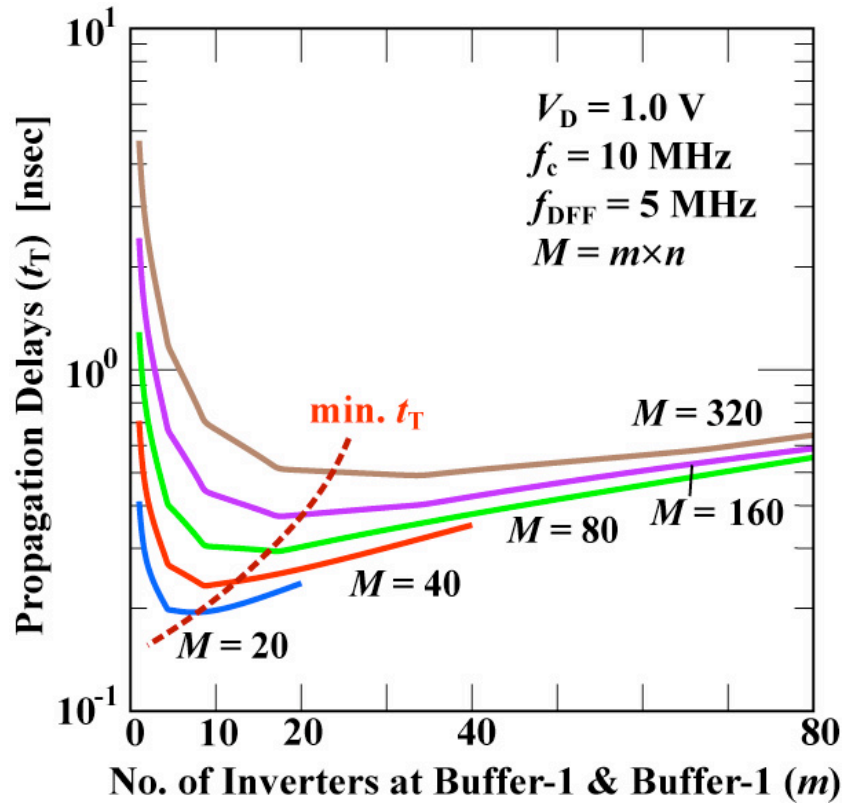
Signal Propagation Delay of 90-nm Register Array Modules (SPICE Simulation)



As m increases,
 t_1 increases,
 t_{2-1}, t_{2-2} decrease,
 t_3 is constant.

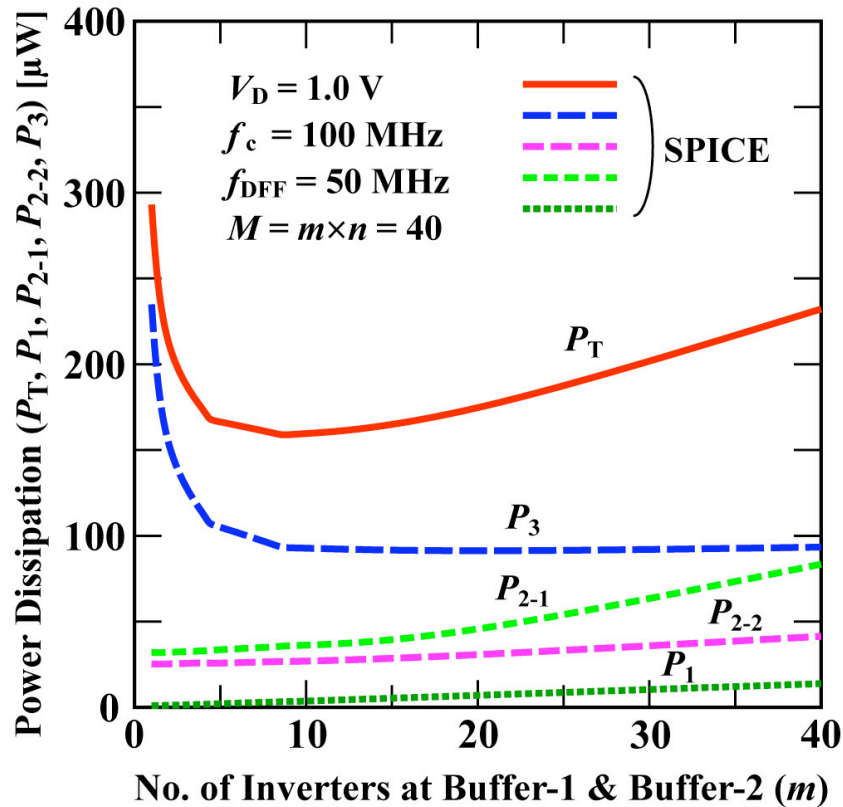


Signal Propagation Delay (t_T) & Optimized m for Minimum t_T of 90-nm Register Array Modules (SPICE Simulation)

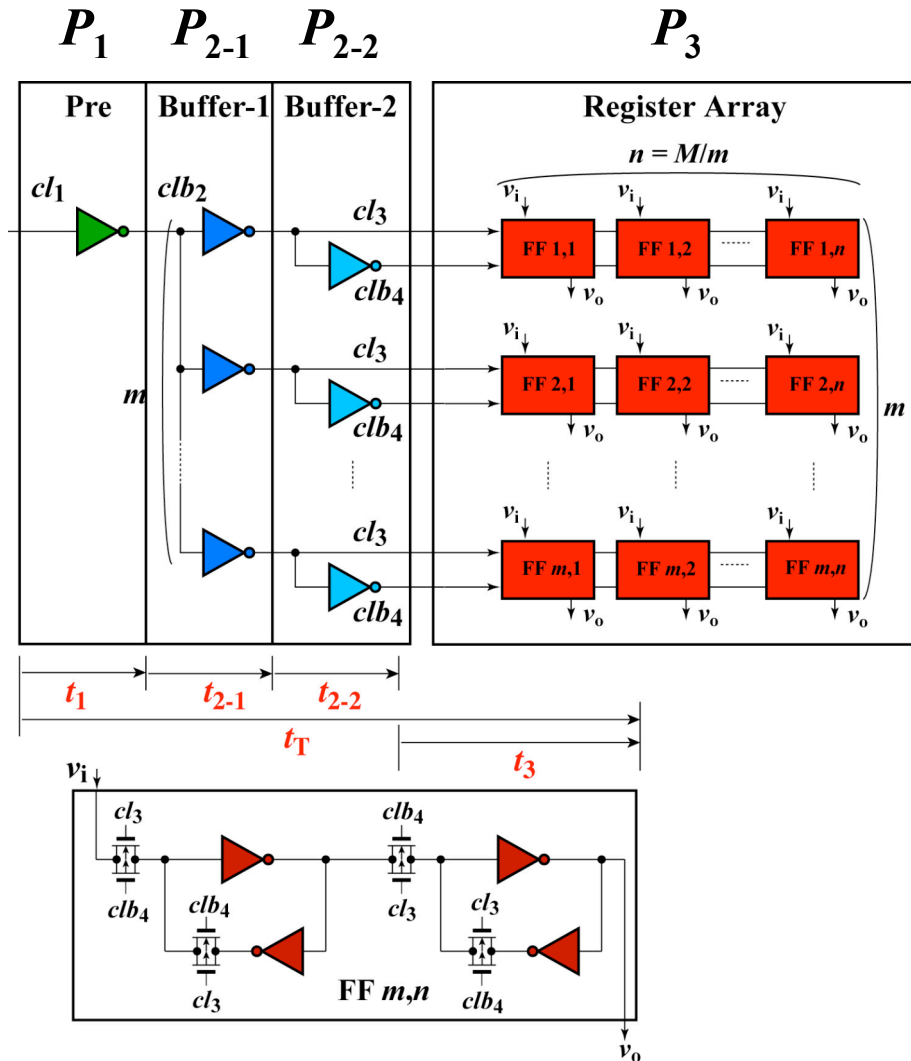


t_T is minimized at
 $m \approx 1.5M^{1/2}$

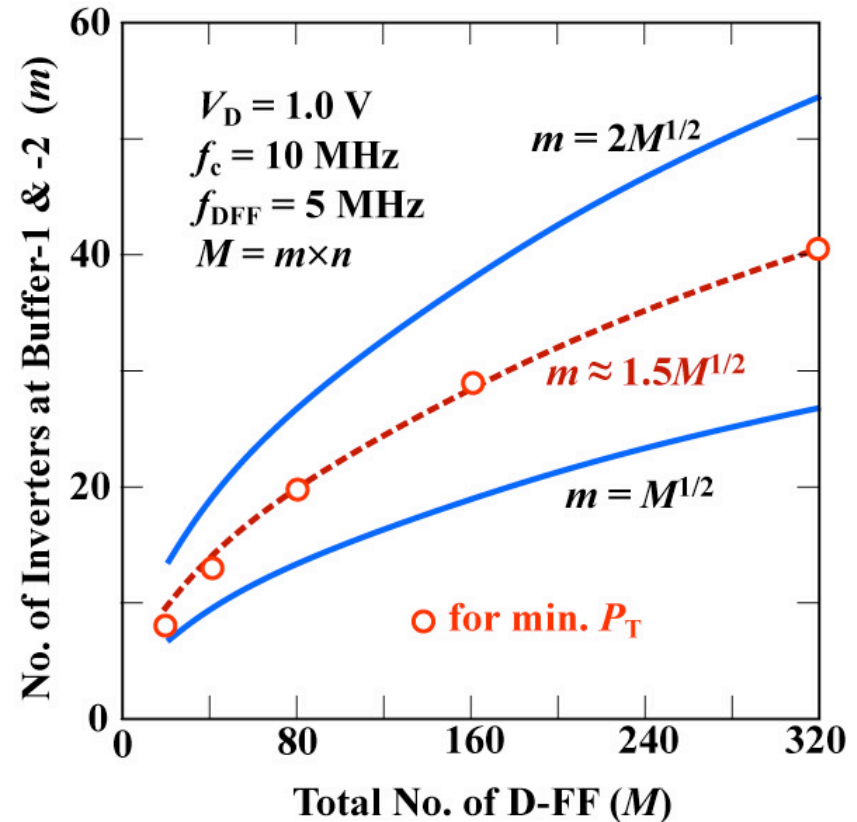
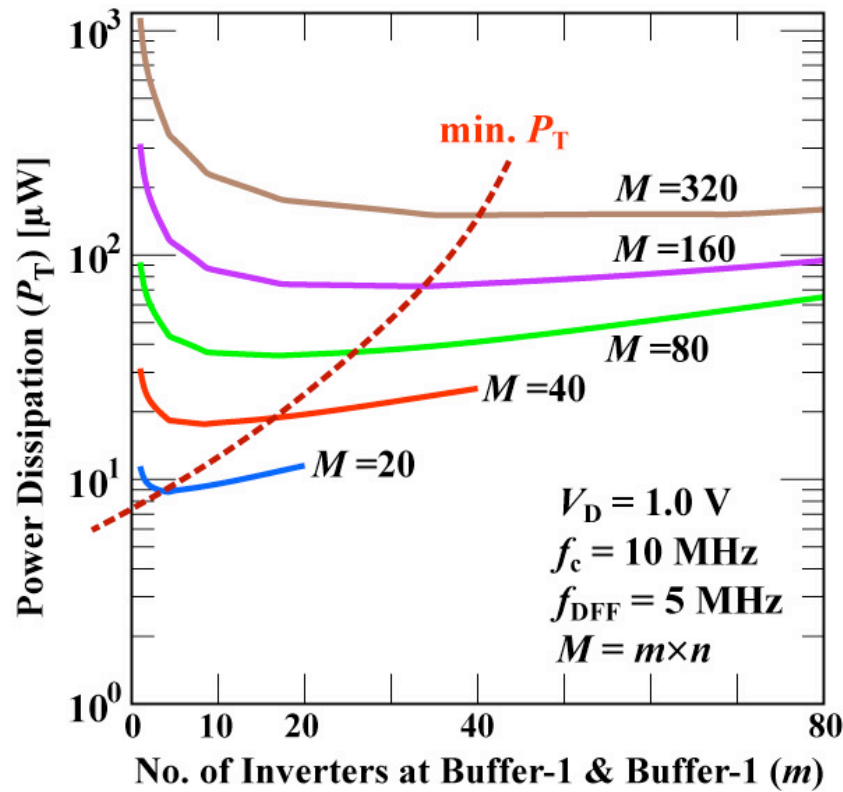
Power Dissipation of 90-nm Register Array Modules (SPICE Simulation)



As m increases
 P_3 decreases
 Others increase.

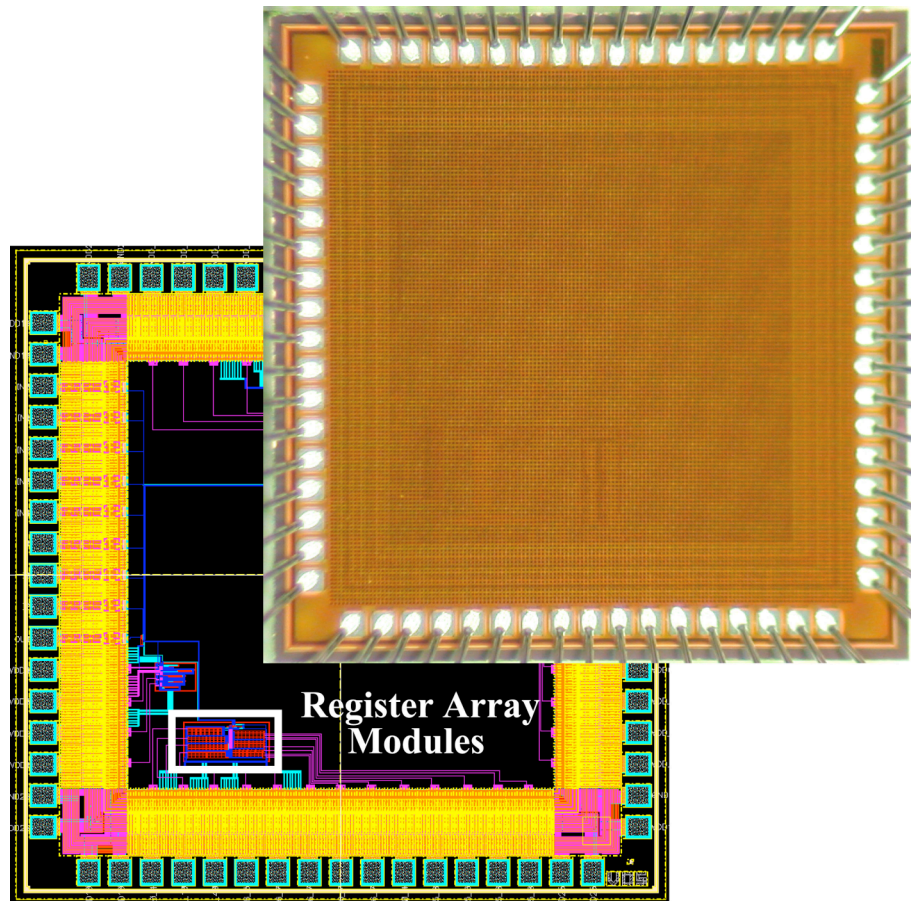


Power Dissipation (P_T) & Optimized m for Minimum P_T of 90-nm Register Array Modules (SPICE Simulation)



P_T is minimized at
 $m \approx 1.5M^{1/2}$

90-nm CMOS LSI Chip with 6 Register Array Modules



Technology:

90-nm, Triple-Well,
6-Layer, Cu, CMOS

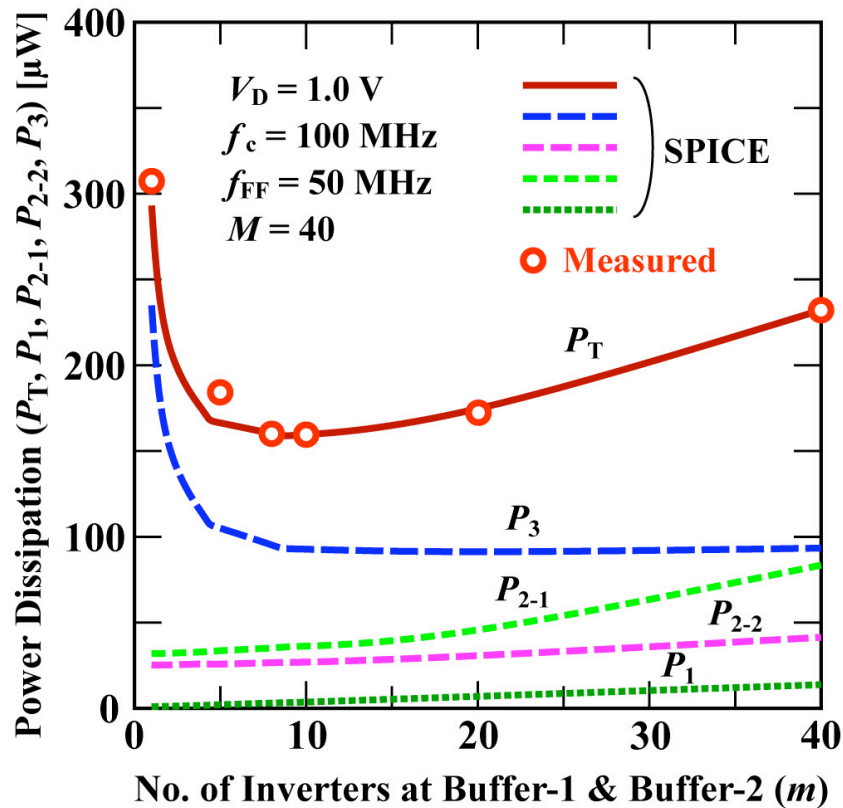
Chip Size:

2.5 mm × 2.5 mm

No. of D-FF ($M = m \times n$) = 40

m	$n = M/m$
1	40
5	8
8	5
10	4
20	2
40	1

Power Dissipation of 90-nm Register Array Modules (Experimental Results)



No. of D-FF ($M = m \times n$) = 40

• Signal Propagation Delay (t_T)

0.95 nsec ($m = 1$)



0.26 nsec (27.4%) ($m = 10$)

• Power Dissipation (P_T)

293.1 μW ($m = 1$)



159.6 μW (54.5%) ($m = 10$)

t_T and P_T are minimized at
 $m \approx 1.5M^{1/2}$